

This listing of claims replaces all prior versions, and listings, of claims in the present application.

Listing of Claims:

1-30. (cancelled)

31. (previously amended) A cathode tip for a cold cathode field emission display device, said tip comprising:

cathode material;

at least one emitter tip with a sharp profile for emitting electrons formed out of said cathode material; and

an emitting layer over each of said at least one tip, wherein said emitting layer is comprised of a metal silicide and has a thickness between 50 and 3000 angstroms.

32. (cancelled)

33. (original) The tip of claim 31 wherein said emitting layer has a thickness of about 100 angstroms.

34. (original) The tip of claim 31 wherein said cathode material is p-doped amorphous silicon.

35. (original) The tip of claim 31 wherein said emitting layer is comprised of iridium silicide.

36. (original) The tip of claim 31 wherein said emitting layer is comprised of nickel silicide.

37. (original) The tip of claim 31 wherein said emitting layer is comprised of platinum silicide.

38. (original) The tip of claim 31 wherein said emitting layer is comprised of palladium silicide.

39. (previously amended) A large area passive matrix cold cathode field emission display device, comprising:

cathode material on a semiconductor substrate;

at least one emitter tip with a sharp profile for emitting electrons formed out of said cathode material;

an emitting layer over each of said at least one tip, wherein said emitting layer is comprised of a metal silicide and has a thickness between 50 and 3000 angstroms.

40. (cancelled)

41. (original) The device of claim 39 wherein said emitting layer has a thickness of about 100 angstroms.

42. (original) The device of claim 39 wherein said cathode material is p-doped amorphous silicon.

43. (original) The device of claim 39 wherein said cathode material is microcrystalline silicon.

44. (original) The device of claim 39 wherein said cathode material is polycrystalline silicon.

45. (original) The device of claim 39 wherein said cathode material is monocrystalline silicon.

46. (original) The device of claim 39 wherein said emitting layer is comprised of iridium silicide.

47. (original) The device of claim 39 wherein said emitting layer is comprised of nickel silicide.

48. (original) The device of claim 39 wherein said emitting layer is comprised of platinum silicide.

49. (original) The device of claim 39 wherein said emitting layer is comprised of palladium silicide.

50. (previously added) A cathode tip for a cold-cathode field emission display device, said tip comprising:

cathode material on a semiconductor substrate;

at least one emitter tip with a sharp profile for emitting electrons formed out of said cathode material;

an annealed emitting layer covering the surface of the emitter tip, wherein said annealed emitting layer has a thickness between 50 and 3000 angstroms, and is comprised of one of the following materials: p-doped amorphous silicon, microcrystalline silicon, monocrystalline silicon, iridium silicide, nickel silicide, platinum silicide and palladium silicide.